

isc Silicon PNP Power Transistor

2SA1659

DESCRIPTION

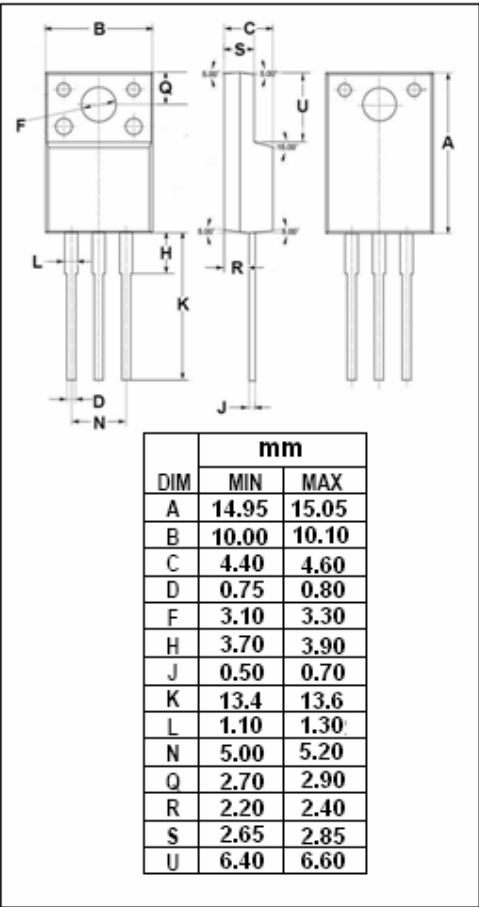
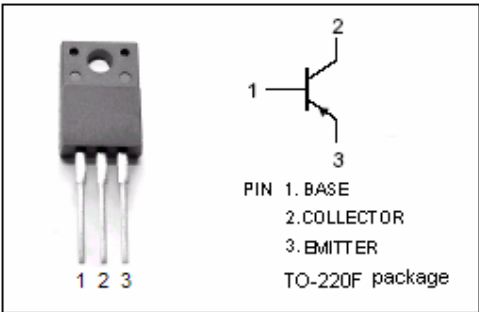
- High Collector-Emitter Breakdown Voltage
 $V_{CEO} = -160V(\text{Min})$
- Complement to Type 2SC4370
- Full-mold package that does not require an insulating board or bushing when mounting.

APPLICATIONS

- Designed for high voltage applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-160	V
V_{CEO}	Collector-Emitter Voltage	-160	V
V_{EBO}	Emitter-Base Voltage	-5.0	V
$I_{C(DC)}$	Collector Current(DC)	-1.5	A
$I_{B(DC)}$	Base Current	-0.15	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}C$	20	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-55~150	$^{\circ}C$



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ELECTRICAL CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -10mA ; I _B = 0	-160			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -500mA; I _B = -50mA			-1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -160V ; I _E =0			-1.0	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5V; I _C =0			-1.0	μ A
h _{FE}	DC Current Gain	I _C = -100mA ; V _{CE} = -5V	70		240	
C _{OB}	Output Capacitance	I _E =0 ; V _{CB} = -10V;f= 1.0MHz		30		pF
f _T	Current-Gain—Bandwidth Product	I _C =-100m A ; V _{CE} = -10V		100		MHz

◆ h_{FE} Classifications

O	Y
70-140	120-240

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